Features:

- ☐ 1.0A, 650V, $R_{DS(on)}$ = 11.0 Ω @V_{GS} = 10 V
- ☐ Low gate charge
- ☐ Low Crss
- ☐ Fast switching
- ☐ 100% avalanche tested
- ☐ Improved dv/dt capability

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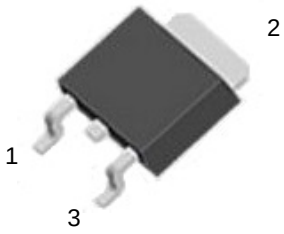
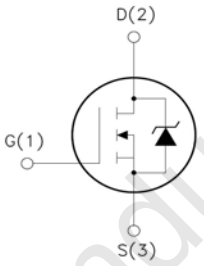




1.Gate (G)
2.Drain (D)
3.Source (S)

Absolute Maximum Ratings (Ta=25℃ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain-Source Voltage		650	V
I_D	Drain Current	T_C=25℃	1	A
		T_C=100℃	0.63	
$V_{GS(TH)}$	Gate Threshold Voltage		±30	V
E_{AS}	Single Pulse Avalanche Energy (note1)		50	mJ
I_{AR}	Avalanche Current (note2)		1	A
P_D	Power Dissipation (Ta=25℃)		28	W
T_j	Junction Temperature(Max)		150	℃
T_{stg}	Storage Temperature		-55~+150	
TL	Maximum lead temperature for soldering purpose,1/8" from case for 5 seconds		300	

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance,Junction to Case	-	4.17	℃/W
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	-	50	℃/W

Electrical Characteristics Tc=25℃ unless other wise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourse Breakdown Voltage	ID=250μA，VGS=0	650	--	--	V
$\triangle BV_{DSS}/\triangle T_J$	Breakdown Voltage Temperature Conficient	I_D=250μA,Reference to 25℃	--	0.4	--	V/℃
IDSS	Zero Gate Voltage Drain Current	Vds=600V, Vgs=0V	--	--	1	μA
		Vds=480V, Tc=125℃			10	μA
IGSSF	Gate-body leakage Current, Forward	Vgs=+30V, Vds=0V	--	--	100	nA
IGSSR	Gate-body leakage Current, Reverse	Vgs=-30V, Vds=0V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Date Threshold Voltage	Id=250uA,Vds=Vgs	2	--	4	V
$R_{DS(on)}$	Static Drain-Sourse On-Resistance	Id=0.5A,Vgs=10V	--	--	11	Ω
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=25V，VGS=0，f=1.0MHz	--	120	150	pF
Coss	Output Capacitance		--	25	60	pF
Crss	Reverse Transfer Capacitance		--	3	4	pF
Switching Characteristics						
Td(on)	Turn-On Delay Time	VDD=300V，ID=1A，RG=25Ω (Note 3,4)	--	5	20	nS
Tr	Turn-On Rise Time		--	25	60	nS
Td(off)	Turn-Off Delay Time		--	7	25	nS
Tf	Turn-Off Fall Time		--	25	60	nS
Qg	Total Gate Charge	VDS=480,VGS=10V，ID=2A (Note 3,4)	--	5	6	pF
Qgs	Gate-Sourse Charge		--	1	--	nC
Qgd	Gate-Drain Charge			2.6	--	nC
Drain-Sourse Diode Characteristics and Maximum Ratings						
I_S	Maximun Continuous Drain-Sourse Diode Forward Current		--	--	1	A
I_{SM}	Maximun Plused Drain-Sourse DiodeForwad Current		--	--	4	A
V_{SD}	Drain-Sourse Diode Forward Voltage	Id=1A	--	--	1.4	V
trr	Reverse Recovery Time	I_S=2A,V_{GS} =0V	--	160	--	nS
Qrr	Reverse Recovery Charge	di_F/dt=100A/μs (Note3)	--	0.30	--	μC

*Notes
1, L=55mH, IAS=1A, VDD=50V, RG=25Ω, Starting TJ =25°C
2, Repetitive Rating : Pulse width limited by maximum junction temperature
3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
4, Essentially Independent of Operating Temperature

Typical Characteristics

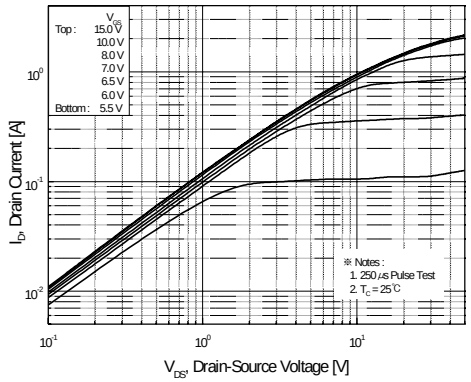


Figure 1. On-Region Characteristics

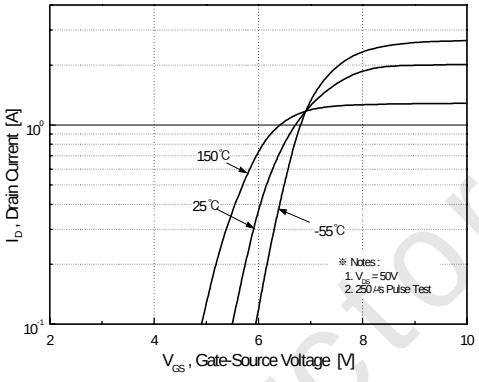


Figure 2. Transfer Characteristics

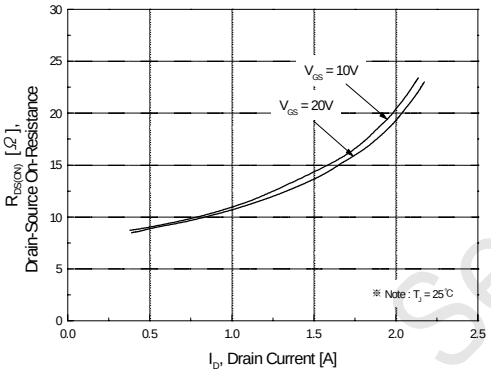


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

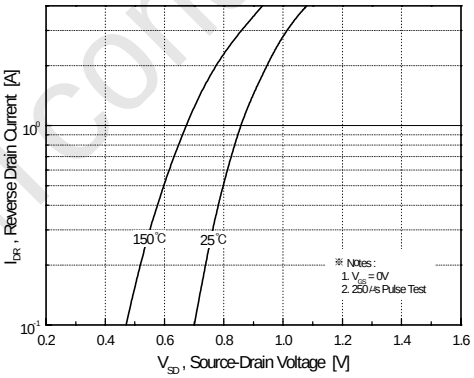


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

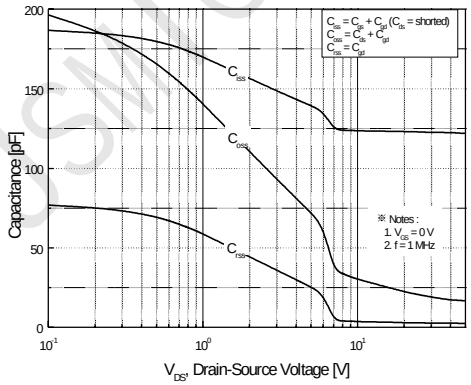


Figure 5. Capacitance Characteristics

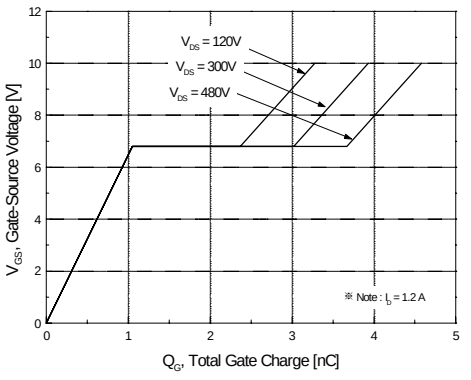


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

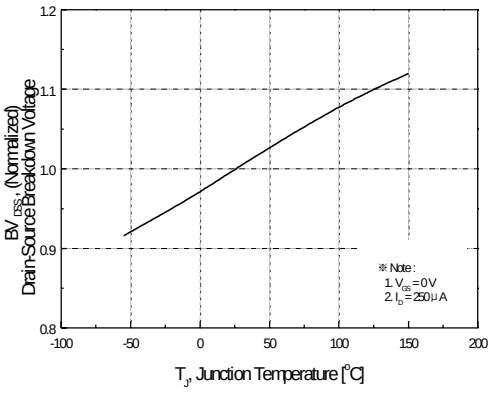


Figure 7. Breakdown Voltage Variation vs. Temperature

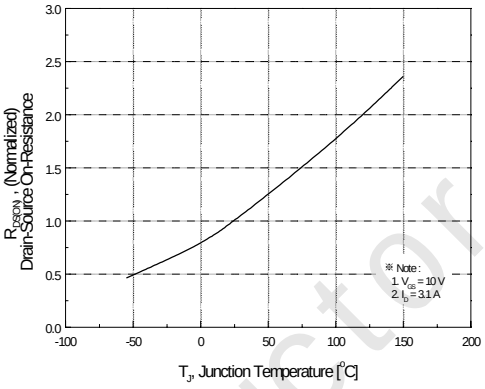


Figure 8. On-Resistance Variation vs. Temperature

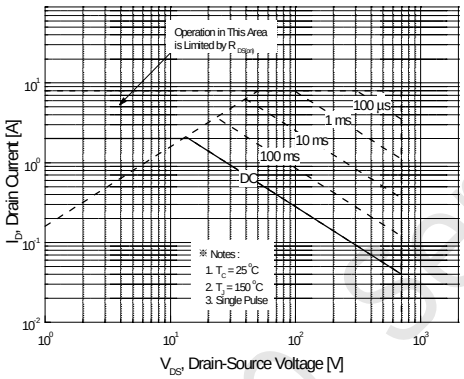


Figure 9. Maximum Safe Operating Area

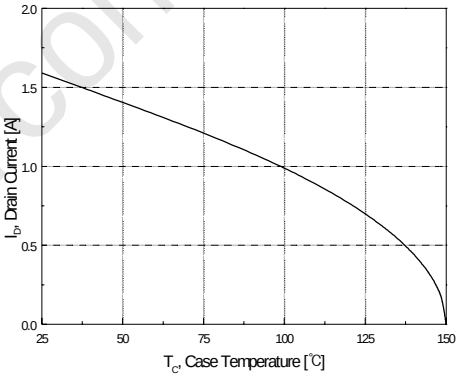


Figure 10. Maximum Drain Current vs. Case Temperature

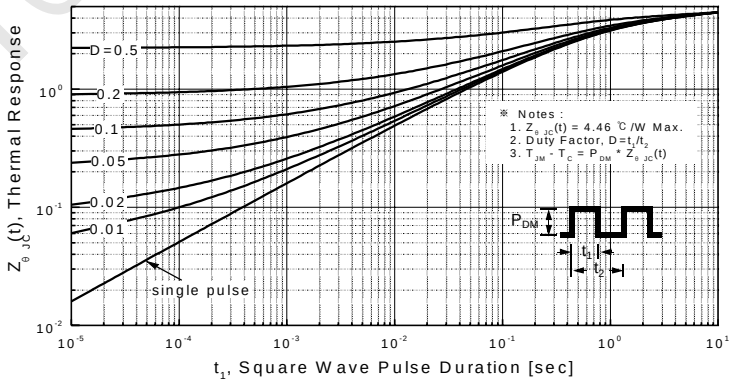
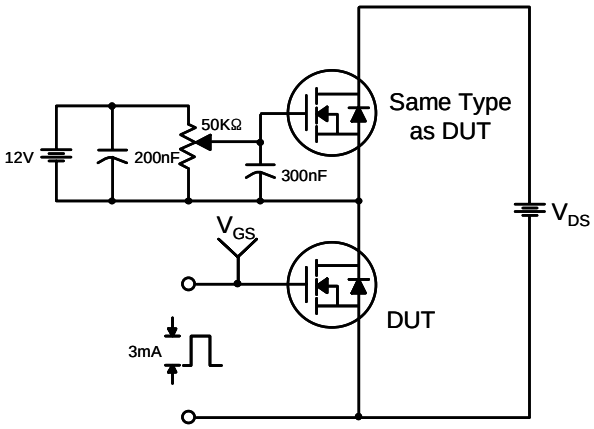
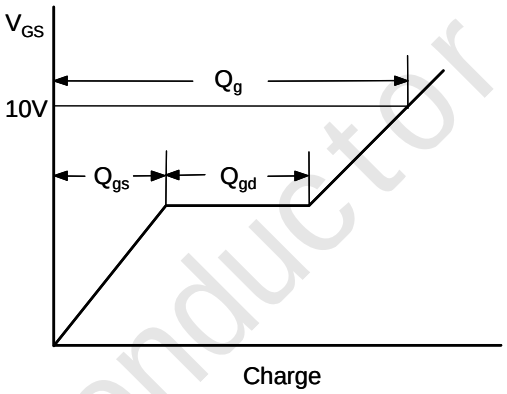


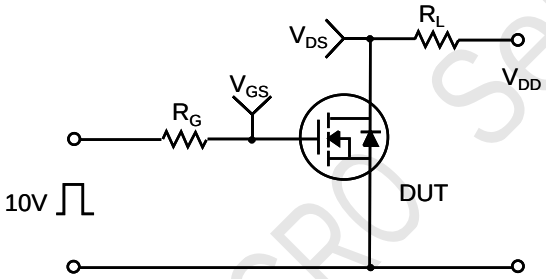
Figure 11. Transient Thermal Response Curve

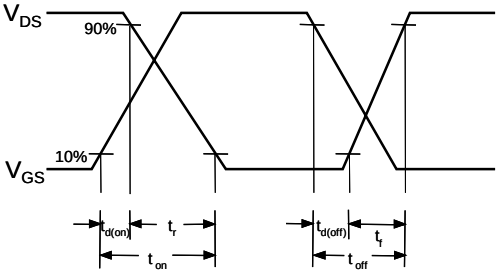
Gate Charge Test Circuit & Waveform



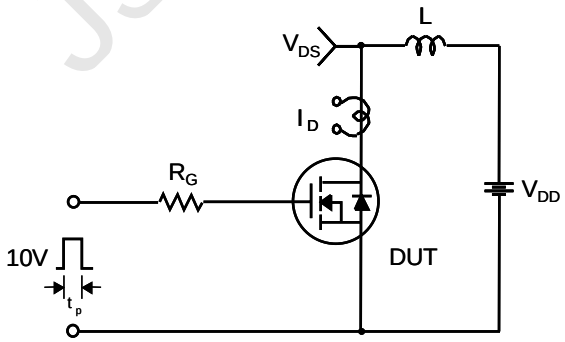


Resistive Switching Test Circuit & Waveforms

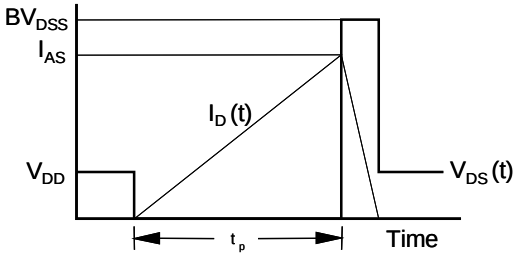




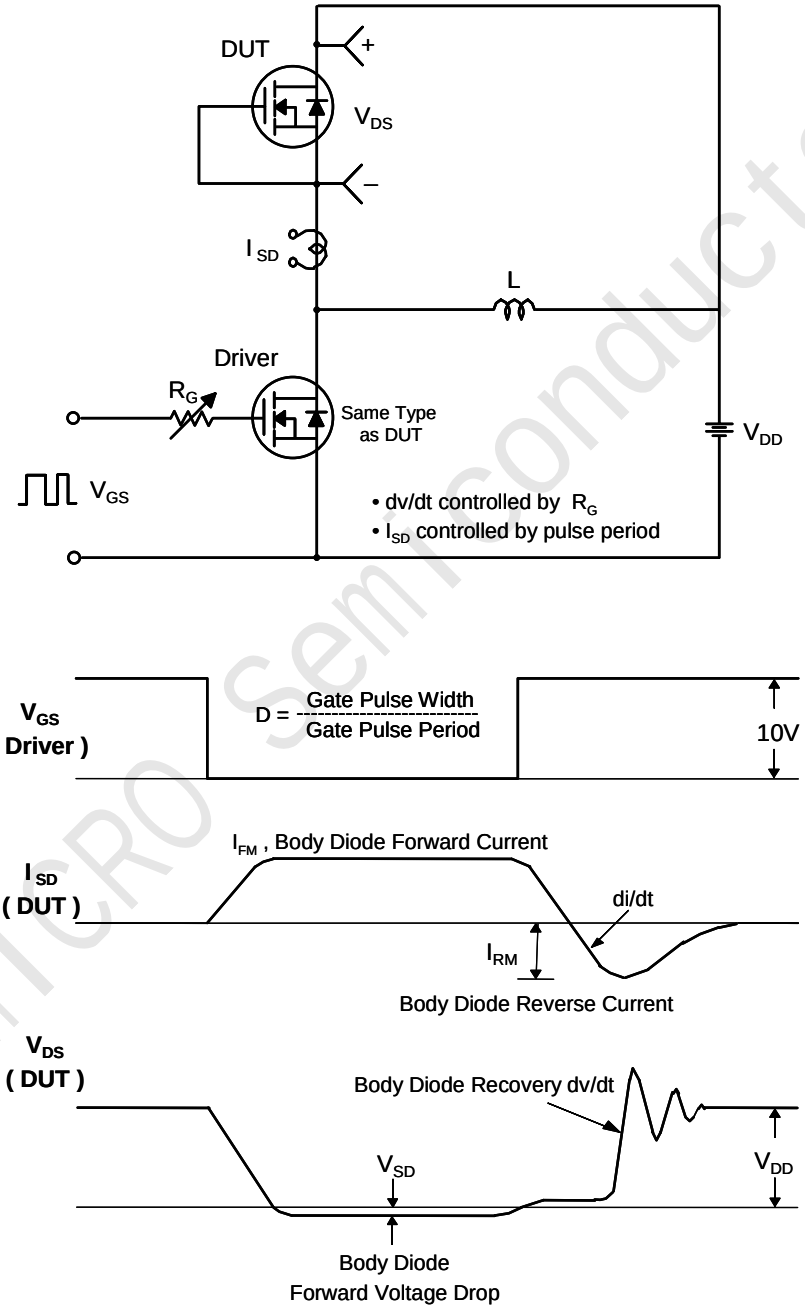
Unclamped Inductive Switching Test Circuit & Waveforms



$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimension

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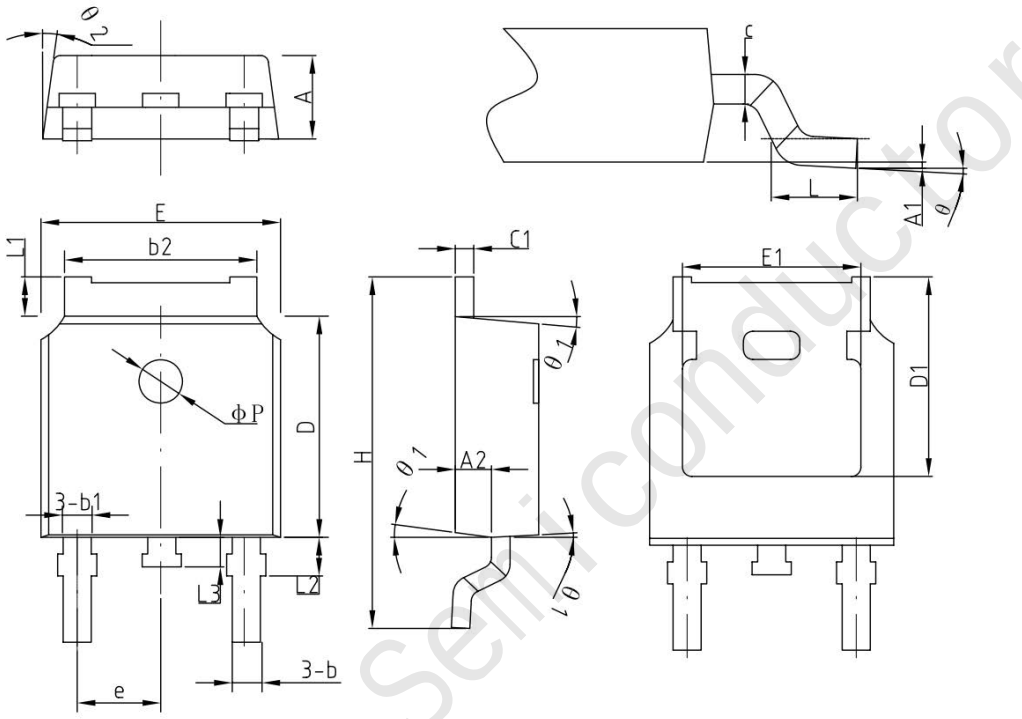
Units：mm



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	2.2	2.30	2.38
A1	0	–	0.10
A2	0.90	1.01	1.10
b	0.71	0.76	0.86
b1		0.76	
b2	5.13	5.33	5.46
c	0.47	0.50	0.60
c1	0.47	0.50	0.60
D	6.0	6.10	6.20
D1	–	5.30	–
E	6.50	6.60	6.70
E1	–	4.80	–
e		2.286BSC	
H	9.70	10.10	10.40
L	1.40	1.50	1.70
L1	0.90	–	1.25
L2		1.05	
L3		0.8	
ΦP		1.2	
θ	0°	–	8°
θ 1	5°	7°	9°
θ 2	5°	7°	9°